Silicon Diode in a SOT-23 Plastic Package.

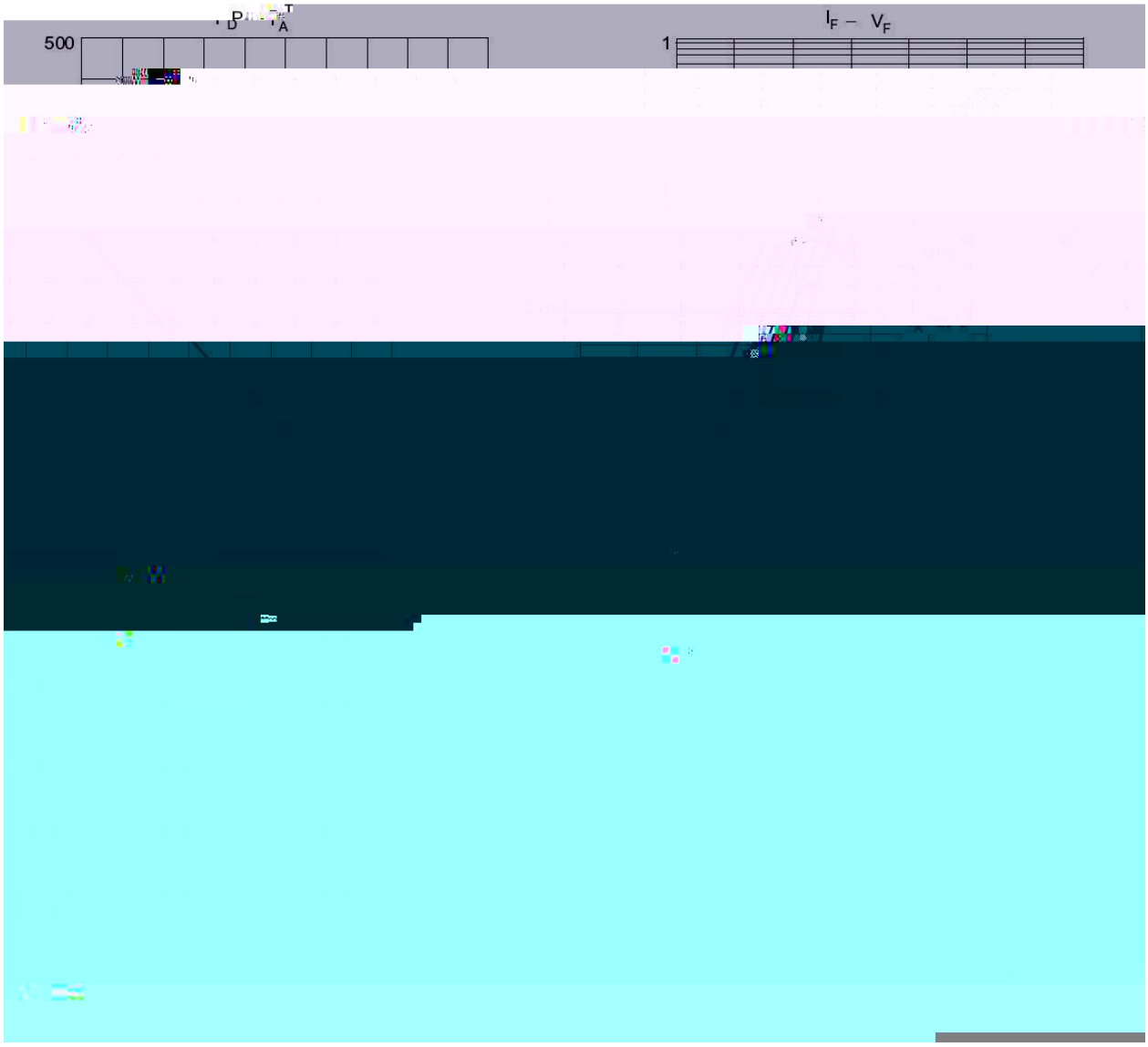
Small signal diode,HF Product.

dd21115025q 0 G [0S ET BT 1 C /P <<O //MCID 28/Lan87 BT /F7316n5231.35 [15185 EMC / 43.42n5231.35 T8* EMC

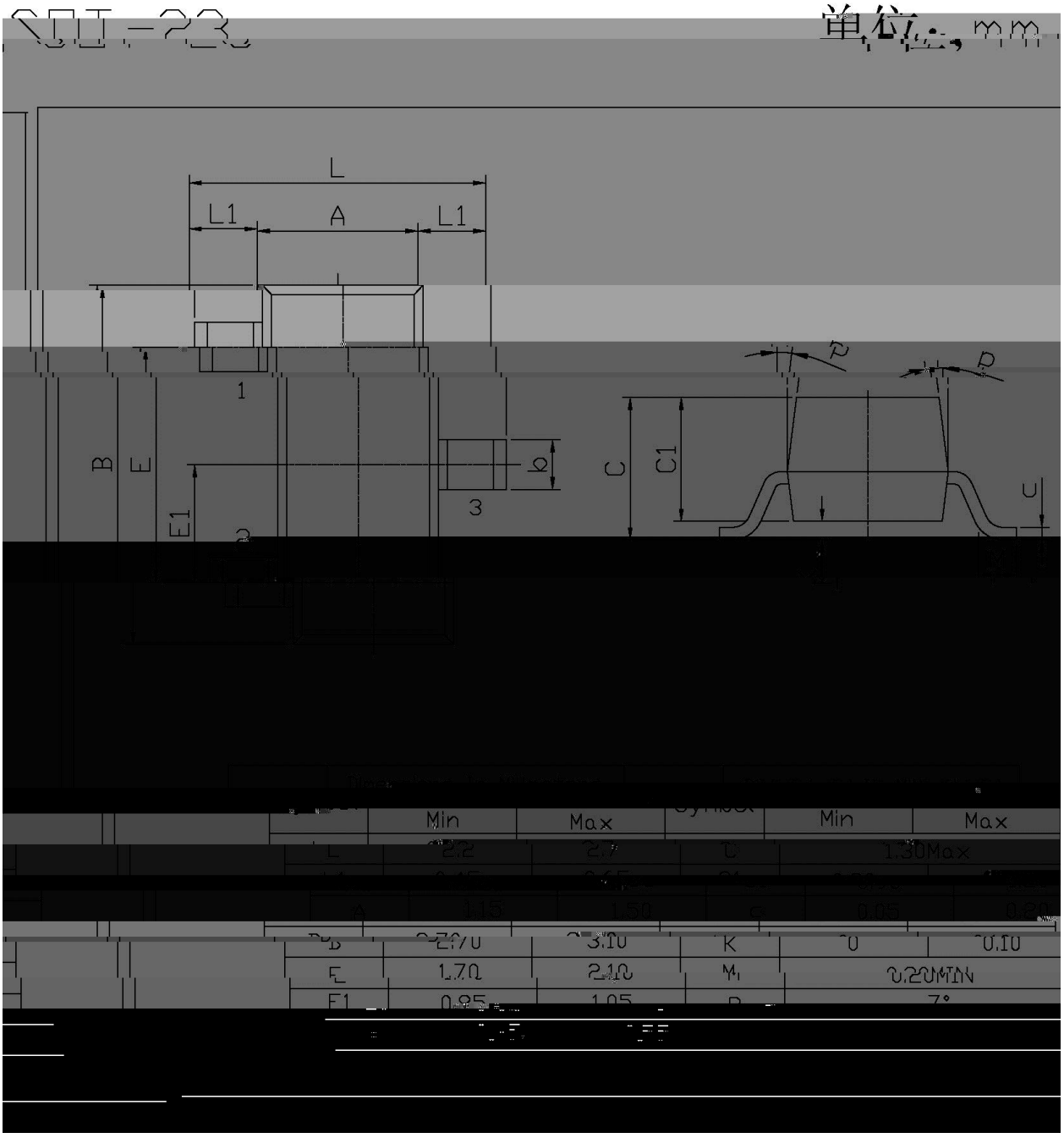
Parameter	Symbol	Rating	Unit
Repetitive Reverse Voltage	V_{RRM}	250	V
Reverse Voltage Working Peak Reverse Voltage	V_R V_{RWM}	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	141	V
Average Rectified Forward Current	I_{FM}	400	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM(1)(pulse\ width=1.0\ uS\ )}$	9.0	A
	$I_{FSM(2)(pulse\ width=100uS)}$	3.0	A
	$I_{FSM(3)(pulse\ width=10ms)}$	1.7	A
Repetitive Peak Forward Surge Current	I_{FRM}	625	mA
Power Dissipation	P_D	350	mW
Thermal Resistance, Junction to Ambient	R	357	/W
Junction and Storage Temperature Range	T_j, T_{stg}	-65 150	

Parameter	Symbol	Test Conditions	gaRiL	

/ Electrical Characteristic Curve



/ Package Dimensions



Min	Max	Min	Max
L 2.2	2.7	C	1.30Max
A 1.15	1.50	c 0.05	0.20
b 2.70	3.10	K 0	0.10
E 1.70	2.10	M_1	0.20MIN
E1 0.85	1.05	θ	7°

BAV23A/C/S

Rev.H Nov.-2023

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Note:

1 150 180 60 90sec;
1.Preheating:150~180 , Time:60~90sec.

2 245 5 5 0.5sec;
2.Peak Temp.:245 5 , Duration:5 0.5sec.

3 2 10 /sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units	Dimension	(unit mm³)